

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("6022672").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/22 09:38
L2	54	(US-20010013161-\$ or US-20010014372-\$ or US-20020009813-\$ or US-20020034595-\$ or US-20020037462-\$ or US-20020187423-\$ or US-20030035087-\$ or US-20030114010-\$ or US-20040050321-\$ or US-20040229441-\$).did. or (US-4855000-\$ or US-4913090-\$ or US-4985722-\$ or US-5151871-\$ or US-5297910-\$ or US-5339128-\$ or US-5547328-\$ or US-5565034-\$ or US-5639301-\$ or US-5686224-\$ or US-5725664-\$ or US-5942013-\$ or US-5970717-\$ or US-5972110-\$ or US-6022672-\$ or US-6077350-\$ or US-6097469-\$ or US-6099643-\$ or US-6183358-\$ or US-6215545-\$ or US-6224274-\$ or US-6261365-\$ or US-6292250-\$ or US-6319322-\$ or US-6341903-\$ or US-6364762-\$).did. or (US-6372042-\$ or US-6414276-\$ or US-6444029-\$ or US-6464789-\$ or US-6485203-\$ or US-6499777-\$ or US-6558053-\$ or US-6572457-\$ or US-6573031-\$ or US-6632281-\$ or US-6676757-\$ or US-6717113-\$).did. or (JP-04021773-\$ or JP-10256344-\$ or JP-10256345-\$ or JP-11031732-\$ or JP-2001308005-\$).did. or (US-20040050321-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/02/22 09:39
L3	26	2 and align\$3	US-PGPUB; USPAT	OR	ON	2005/02/22 11:59
L4	18	2 and (align\$3 same expos\$4)	US-PGPUB; USPAT	OR	ON	2005/02/22 09:39
L5	6	2 and dehumid\$7	US-PGPUB; USPAT	OR	ON	2005/02/22 11:16
L6	0	(118/719.ccls. 156/345.31.ccls. "156"/.45.32.ccls.) and (dehumid\$7 with (transfer\$4 transport\$4 convey\$4))	US-PGPUB; USPAT	OR	ON	2005/02/22 11:16
L7	0	(118/719.ccls. 156/345.31.ccls. "156"/345.32.ccls.) and (dehumid\$7 with (transfer\$4 transport\$4 convey\$4))	US-PGPUB; USPAT	OR	ON	2005/02/22 11:17
L8	20	dehumid\$7 with (transfer\$4 transport\$4 convey\$4) with (wafer substrate semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2005/02/22 11:17
L9	17	dehumid\$7 with (transfer\$4 transport\$4 convey\$4) with (wafer substrate semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/22 11:28
L10	1	("5932380").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/22 11:55
L11	2377	aligner with expos\$3	EPO; JPO; DERWENT	OR	ON	2005/02/22 11:56
L17	17	2 and (interface with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/22 12:02
L18	8773	(interface with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/22 12:02
L19	69	("interface section" with cooling)	US-PGPUB; USPAT	OR	ON	2005/02/22 12:02
L20	94	("interface section" with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/22 13:08
L21	48	(118/715-733.ccls. 156/345.\$ccls.) and (cool\$3 with gas with regulat\$3 with (moisture temperature humidity))	US-PGPUB; USPAT	OR	ON	2005/02/22 13:37
L22	1	118/58-69.ccls. and (cool\$3 with gas with regulat\$3 with (moisture temperature humidity))	US-PGPUB; USPAT	OR	ON	2005/02/22 13:30
L24	200	kitano-junichi.in. matsuyama-yuji.in. kitano-takahiro.in. matsui-hidefumi.in. suzuki-yo.in. yamashita-masami.in. aoyama-toru.in. iwaki-hiroyuki.in. shimura-satoru.in. deguchi-msatoshi.in. yoshihara-kousuke.in. iida-naruaki.in.	US-PGPUB; USPAT	OR	ON	2005/02/22 14:51
L25	57	24 and (humid\$7 dehumid\$7 moisture)	US-PGPUB; USPAT	OR	ON	2005/02/22 14:52

L26	17	24 and (humid\$7 dehumid\$7 moisture).dm.	US-PGPUB; USPAT	OR	ON	2005/02/22 14:53
S7	1	10/649,780	US-PGPUB; USPAT	OR	ON	2005/02/22 09:38
S8	131	(118/719.cds. 156/345.31.cds. 156/345.32.cds. 414-935-941.cds.) and (resist and heat\$3 and cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/21 14:10
S9	22	(118/719.cds. 156/345.31.cds. 156/345.32.cds. 414-935-941.cds.) and (reaction with inhibit\$3)	US-PGPUB; USPAT	OR	ON	2005/02/18 16:35
S10	6	(118/719.cds. 156/345.31.cds. 156/345.32.cds. 414-935-941.cds.) and (resist with resolution)	US-PGPUB; USPAT	OR	ON	2005/02/18 16:35
S11	217	(118/719.cds. 156/345.31.cds. 156/345.32.cds. 414/935-941.cds.) and (resist and heat\$3 and cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/18 16:35
S12	23	(118/719.cds. 156/345.31.cds. 156/345.32.cds. 414/935-941.cds.) and (reaction with inhibit\$3)	US-PGPUB; USPAT	OR	ON	2005/02/18 16:35
S13	7	(118/719.cds. 156/345.31.cds. 156/345.32.cds. 414/935-941.cds.) and (resist with resolution)	US-PGPUB; USPAT	OR	ON	2005/02/18 16:35
S14	5	("6097469").URPN.	USPAT	OR	ON	2005/02/18 16:41
S15	1	("6632281").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/18 16:41
S16	6	("5725664" "5785741" "5876280" "5952149" "6054181" "6467976").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/18 16:43
S17	23	("5725664").URPN.	USPAT	OR	ON	2005/02/18 16:49
S18	3	(118/719.cds. 156/345.31.cds. 156/345.32.cds. 414-935-941.cds.) and (resist same (inhibit\$3 prevent\$3) same cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/18 17:12
S19	892	(resist same (inhibit\$3 prevent\$3) same cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/18 17:12
S20	114	(resist same (inhibit\$3 prevent\$3) same cool\$3 same transfer\$4)	US-PGPUB; USPAT	OR	ON	2005/02/18 17:49
S21	9	("5970717").URPN.	USPAT	OR	ON	2005/02/18 17:31
S22	75	(resist same (inhibit\$3 prevent\$3) same transfer\$4) and "118"/\$.cds.	US-PGPUB; USPAT	OR	ON	2005/02/18 17:50
S23	61	S22 not S20	US-PGPUB; USPAT	OR	ON	2005/02/18 17:50
S24	2	"09076685"	EPO; JPO; DERWENT	OR	ON	2005/02/18 18:32
S25	157	tateyama-kiyohisa.in.	EPO; JPO; DERWENT	OR	ON	2005/02/18 18:31
S26	0	"9076685"	EPO; JPO; DERWENT	OR	ON	2005/02/18 18:32
S27	1	(118/719.cds. 156/345.31.cds. 156/345.32.cds. 414-935-941.cds.) and (dehumidif\$7)	US-PGPUB; USPAT	OR	ON	2005/02/21 14:11
S28	3	(118/719.cds. 156/345.31.cds. 156/345.32.cds. 414/935-941.cds.) and (dehumidif\$7)	US-PGPUB; USPAT	OR	ON	2005/02/21 14:13
S29	13	(substrate wafer semiconductor workpiece) and (resist same dehumidif\$7)	US-PGPUB; USPAT	OR	ON	2005/02/21 14:37
S30	121	(substrate wafer semiconductor workpiece) and ("resolution reaction")	US-PGPUB; USPAT	OR	ON	2005/02/21 14:45
S31	4	resist same ("resolution reaction")	US-PGPUB; USPAT	OR	ON	2005/02/21 14:46
S32	2	resist same ("resolution reaction")	EPO; JPO; DERWENT	OR	ON	2005/02/21 14:50
S33	1657482	transfer\$4 convey\$4 transport\$4 mov\$4 with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction	EPO; JPO; DERWENT	OR	ON	2005/02/21 14:51

S34	85	(transfer\$4 convey\$4 transport\$4 mov\$4) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction	EPO; JPO; DERWENT	OR	ON	2005/02/21 14:52
S35	9	(transfer\$4 convey\$4 transport\$4 mov\$4) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 17:45
S36	39	(transfer\$4 convey\$4 transport\$4 mov\$4) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2005/02/21 15:19
S37	6	(resist) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2005/02/21 15:29
S38	5	("5254170" "5609689" "6143083" "6224274" "6235634").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/21 15:25
S39	3	(resist) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:30
S40	0	(acid with amplif\$7) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:30
S41	0	(acid with amplif\$7) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:31
S42	2	(acid with amplif\$7) with (cool\$3) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4)	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:31
S43	882	(acid with amplif\$7) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4)	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:31
S44	84	(acid with amplif\$7) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with resist	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:33
S45	276	(acid with amplif\$7) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with resist	US-PGPUB; USPAT	OR	ON	2005/02/21 15:32
S46	2	(acid with amplif\$7) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with resist with cool\$3	US-PGPUB; USPAT	OR	ON	2005/02/21 15:33
S47	0	(acid with amplif\$7) with (cool\$3) with resist	EPO; JPO; DERWENT	OR	ON	2005/02/21 15:34
S48	3	(acid with amplif\$7) with (cool\$3) with resist	US-PGPUB; USPAT	OR	ON	2005/02/21 15:34
S49	16	(acid with amplif\$7) same (cool\$3) same resist	US-PGPUB; USPAT	OR	ON	2005/02/21 15:44
S50	96	(resolv\$3 resolution solubilization) same (cool\$3) same resist	US-PGPUB; USPAT	OR	ON	2005/02/21 15:45
S51	18	("5151871").URPN.	USPAT	OR	ON	2005/02/21 16:26
S52	1	("6414276").PN.	US-PGPUB; USPAT	OR	OFF	2005/02/21 16:26
S53	11	("4518848" "5452177" "5538758" "5595241" "5730803" "5775416" "5811762" "6072163" "6080969" "6091060" "6270580").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/21 16:26
S54	248	(transfer\$4 convey\$4 transport\$4 mov\$4) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	EPO; JPO; DERWENT	OR	ON	2005/02/21 17:45
S55	738	(transfer\$4 convey\$4 transport\$4 mov\$4) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4) with reaction with (substrate wafer semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2005/02/21 17:46
S56	808	(transfer\$4 convey\$4 transport\$4 mov\$4) with (hault\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction with (substrate wafer semiconductor workpiece)	US-PGPUB; USPAT	OR	ON	2005/02/21 17:47

S57	283	((transfer\$4 convey\$4 transport\$4 mov\$4) with (halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction with (substrate wafer semiconductor workpiece))	EPO; JPO; DERWENT	OR	ON	2005/02/21 17:47
S58	5	((transfer\$4 convey\$4 transport\$4 mov\$4) with (halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction with (substrate wafer semiconductor workpiece)) same resist	EPO; JPO; DERWENT	OR	ON	2005/02/21 19:01
S59	16	((transfer\$4 convey\$4 transport\$4 mov\$4) with (halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction with (substrate wafer semiconductor workpiece)) same resist	US-PGPUB; USPAT	OR	ON	2005/02/21 17:55
S60	120	((transfer\$4 convey\$4 transport\$4 mov\$4) with (halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction with (substrate wafer semiconductor workpiece)) and resist	US-PGPUB; USPAT	OR	ON	2005/02/21 17:56
S61	104	S60 not S59	US-PGPUB; USPAT	OR	ON	2005/02/21 17:56
S62	5	("4717645" "4924800" "4985722" "5339128" "5401316").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/21 18:46
S63	4	("6022672").URPN.	USPAT	OR	ON	2005/02/21 18:49
S64	1	118/69.ccls. and (((halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with reaction) same resist)	US-PGPUB; USPAT	OR	ON	2005/02/21 19:03
S65	133	118/69.ccls. and (((halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3))	US-PGPUB; USPAT	OR	ON	2005/02/21 19:03
S66	3	118/69.ccls. and (((halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3 with resist))	US-PGPUB; USPAT	OR	ON	2005/02/21 19:04
S67	133	118/69.ccls. and ((halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/21 19:05
S68	0	118/69.ccls. and ((halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3 with reaction)	US-PGPUB; USPAT	OR	ON	2005/02/21 19:05
S69	5	118/58-69.ccls. and ((halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3 with reaction)	US-PGPUB; USPAT	OR	ON	2005/02/22 13:29
S70	325	118/58-69.ccls. and ((halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/21 19:08
S71	45	118/58-69.ccls. and ((halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3) and resist	US-PGPUB; USPAT	OR	ON	2005/02/21 19:35
S72	325	118/58-69.ccls. and ((halt\$3 end\$3 limit\$3 inhibit\$3 prevent\$3 deter\$4 stop\$3 restrict\$3) with cool\$3)	US-PGPUB; USPAT	OR	ON	2005/02/21 19:36